

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type ( $\pi$ -MOSIII)

# 2SK2611

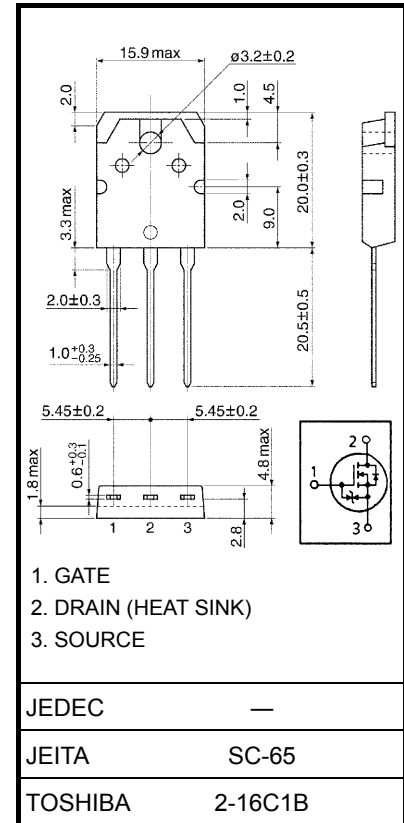
DC-DC Converter, Relay Drive and Motor Drive Applications

Unit: mm

- Low drain-source ON resistance :  $R_{DS(ON)} = 1.1 \Omega$  (typ.)
- High forward transfer admittance :  $|Y_{fs}| = 7.0 \text{ S}$  (typ.)
- Low leakage current :  $I_{DSS} = 100 \mu\text{A}$  (max) ( $V_{DS} = 720 \text{ V}$ )
- Enhancement-mode :  $V_{th} = 2.0 \sim 4.0 \text{ V}$  ( $V_{DS} = 10 \text{ V}$ ,  $I_D = 1 \text{ mA}$ )

## Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Characteristics	Symbol	Rating	Unit
Drain-source voltage	$V_{DSS}$	900	V
Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )	$V_{DGR}$	900	V
Gate-source voltage	$V_{GSS}$	$\pm 30$	V
Drain current	DC (Note 1)	$I_D$	9 A
	Pulse (Note 1)	$I_{DP}$	27 A
Drain power dissipation ( $T_c = 25^\circ\text{C}$ )	$P_D$	150	W
Single pulse avalanche energy (Note 2)	$E_{AS}$	663	mJ
Avalanche current	$I_{AR}$	9	A
Repetitive avalanche energy (Note 3)	$E_{AR}$	15	mJ
Channel temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage temperature range	$T_{stg}$	$-55 \sim 150$	$^\circ\text{C}$



Weight: 4.6 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

## Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	0.833	$^\circ\text{C} / \text{W}$
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	50	$^\circ\text{C} / \text{W}$

Note 1: Please use devices on condition that the channel temperature is below  $150^\circ\text{C}$ .

Note 2:  $V_{DD} = 90 \text{ V}$ ,  $T_{ch} = 25^\circ\text{C}$  (initial),  $L = 15 \text{ mH}$ ,  $R_G = 25 \Omega$ ,  $I_{AR} = 9 \text{ A}$

Note 3: Repetitive rating: Pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device.  
Please handle with caution.

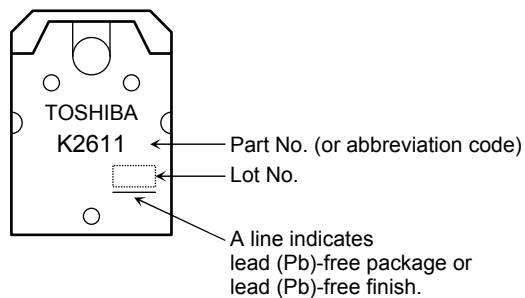
**Electrical Characteristics (Ta = 25°C)**

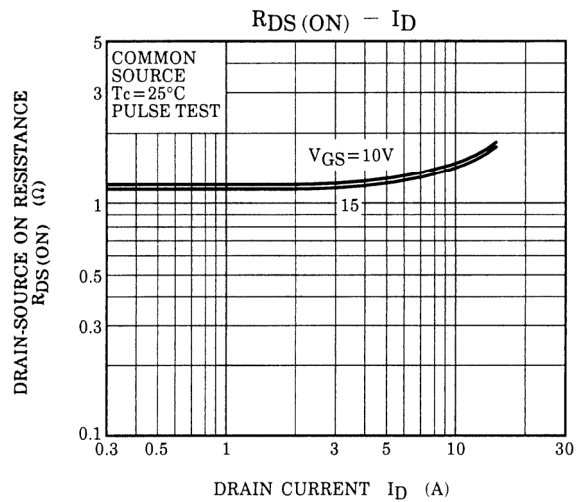
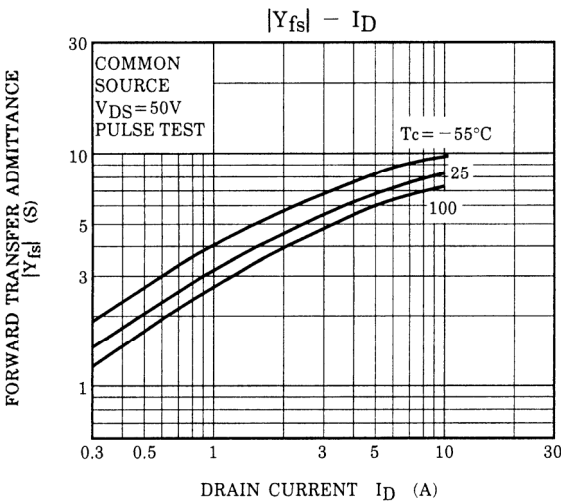
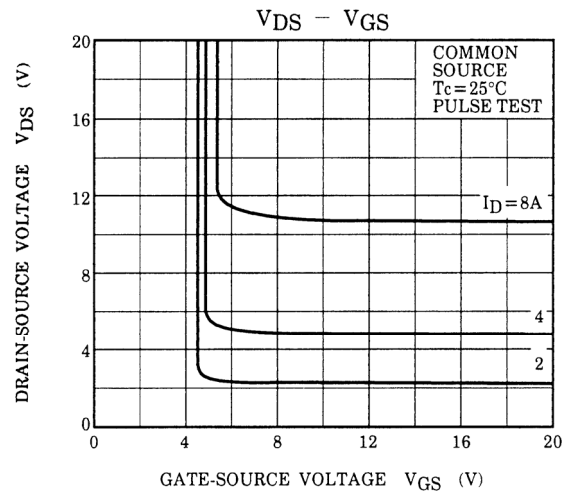
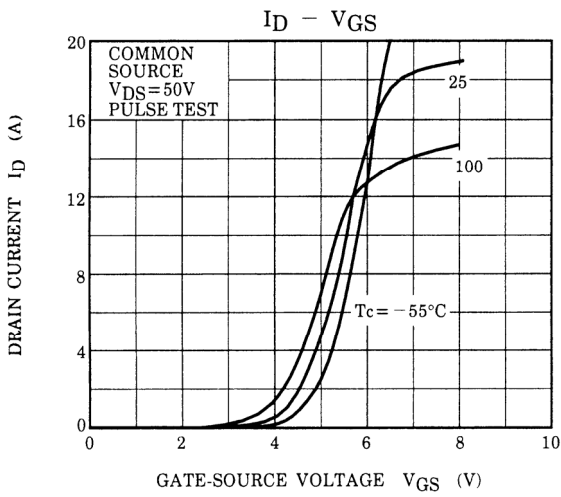
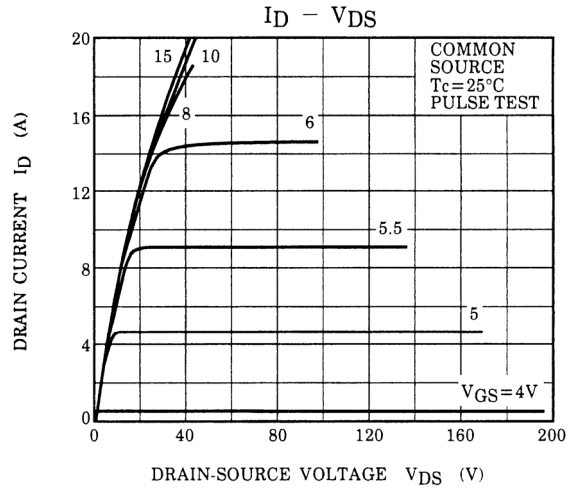
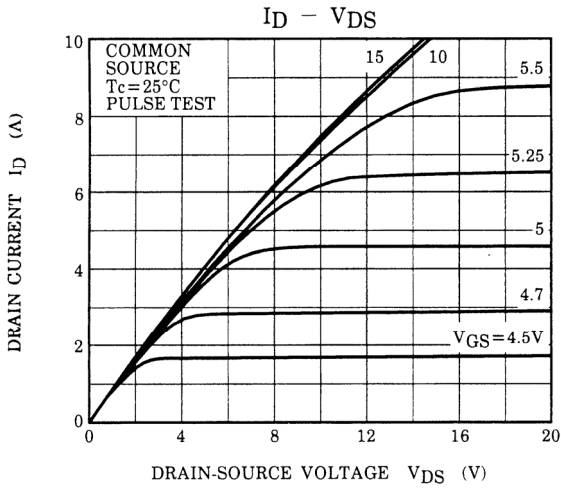
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		$I_{GSS}$	$V_{GS} = \pm 30\text{ V}, V_{DS} = 0\text{ V}$	—	—	$\pm 10$	$\mu\text{A}$
Gate-source breakdown voltage		$V_{(BR)GSS}$	$I_G = \pm 10\ \mu\text{A}, V_{DS} = 0\text{ V}$	$\pm 30$	—	—	V
Drain cut-off current		$I_{DSS}$	$V_{DS} = 720\text{ V}, V_{GS} = 0\text{ V}$	—	—	100	$\mu\text{A}$
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	900	—	—	V
Gate threshold voltage		$V_{th}$	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	2.0	—	4.0	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 4\text{ A}$	—	1.1	1.4	$\Omega$
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 15\text{ V}, I_D = 4\text{ A}$	3.0	7.0	—	S
Input capacitance		$C_{iss}$	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	2040	—	pF
Reverse transfer capacitance		$C_{rss}$		—	45	—	
Output capacitance		$C_{oss}$		—	190	—	
Switching time	Rise time	$t_r$		—	25	—	ns
	Turn-on time	$t_{on}$		—	60	—	
	Fall time	$t_f$		—	20	—	
	Turn-off time	$t_{off}$		—	95	—	
Total gate charge (gate-source plus gate-drain)		$Q_g$	$V_{DD} \approx 400\text{ V}, V_{GS} = 10\text{ V}, I_D = 9\text{ A}$	—	58	—	nC
Gate-source charge		$Q_{gs}$		—	32	—	
Gate-drain ("miller") Charge		$Q_{gd}$		—	26	—	

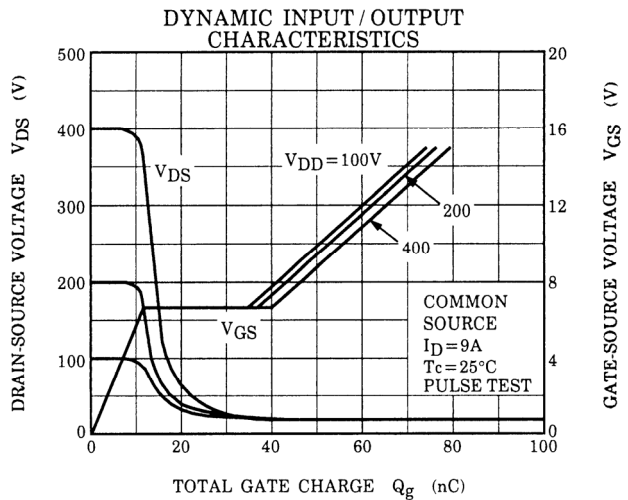
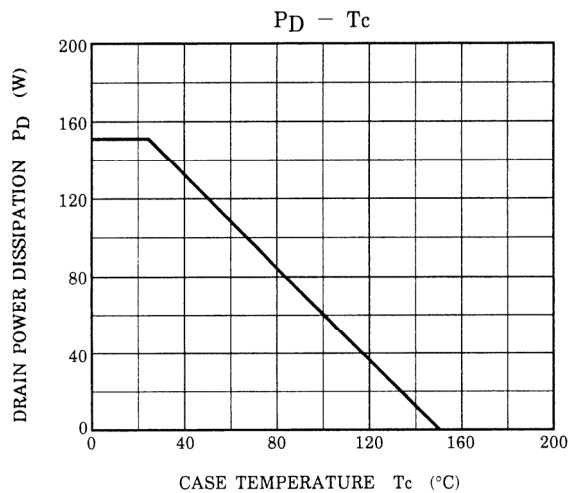
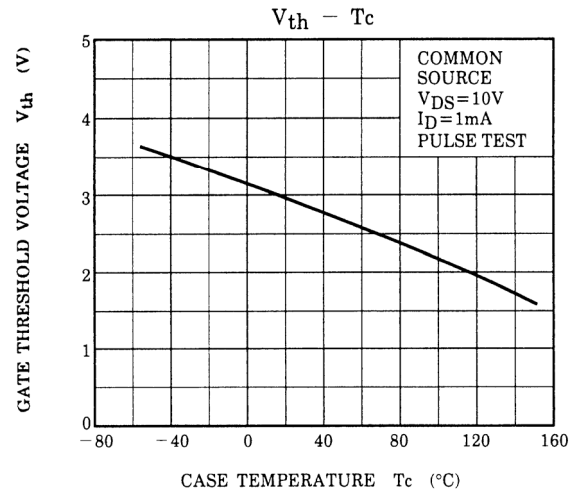
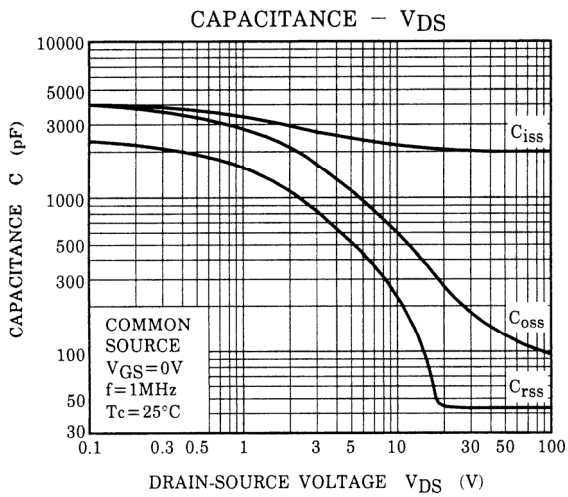
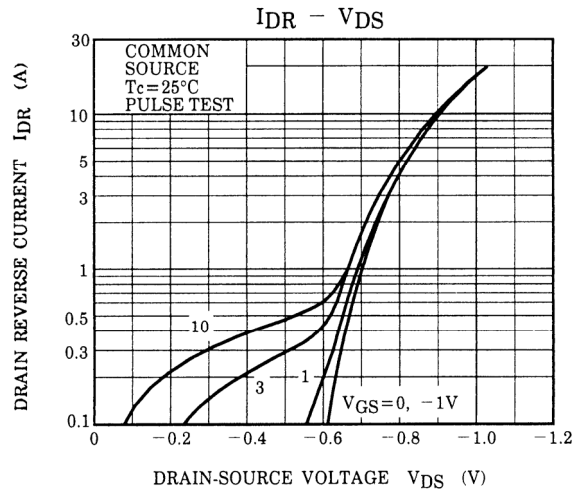
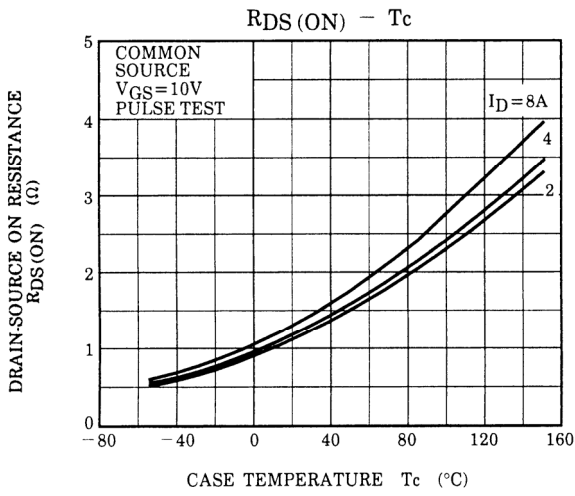
**Source-Drain Ratings and Characteristics (Ta = 25°C)**

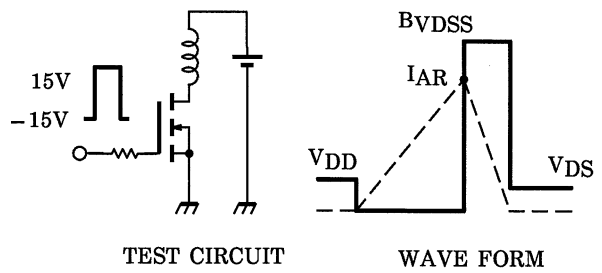
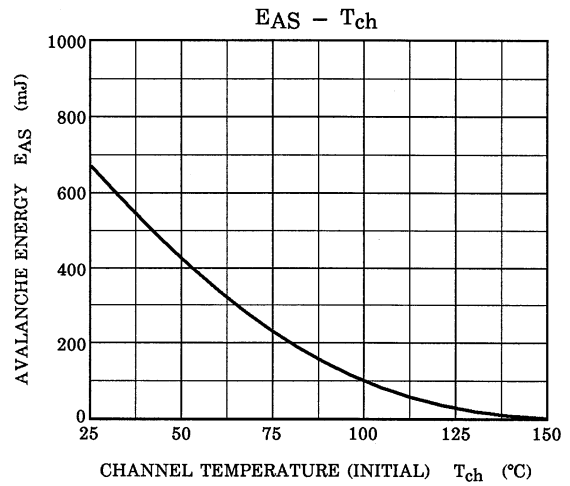
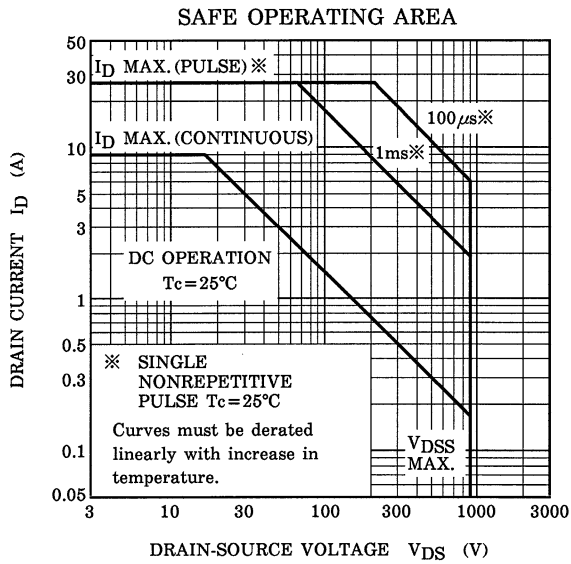
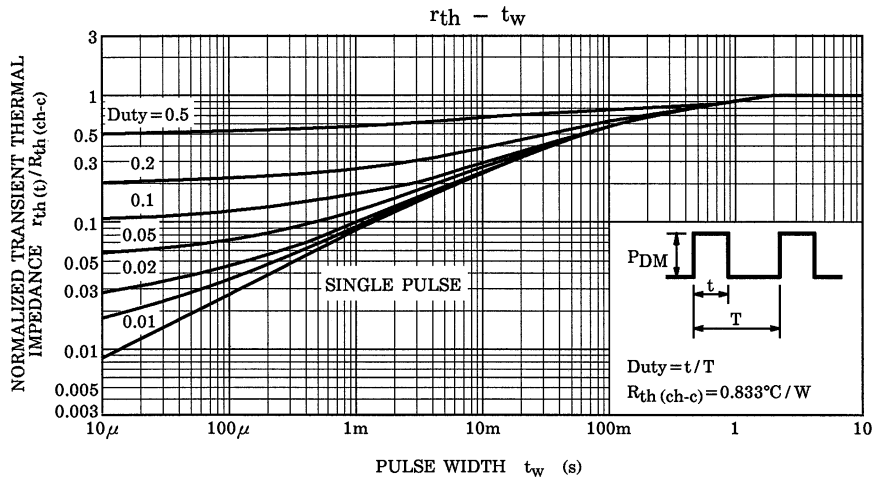
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	$I_{DR}$	—	—	—	9	A
Pulse drain reverse current (Note 1)	$I_{DRP}$	—	—	—	27	A
Forward voltage (diode)	$V_{DSF}$	$I_{DR} = 9\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.9	V
Reverse recovery time	$t_{rr}$	$I_{DR} = 9\text{ A}, V_{GS} = 0\text{ V}, dI_{DR} / dt = 100\text{ A} / \mu\text{s}$	—	1.6	—	$\mu\text{s}$
Reverse recovery charge	$Q_{rr}$		—	20	—	$\mu\text{C}$

**Marking**









$R_G = 25 \Omega$   
 $V_{DD} = 90 \text{ V}, L = 15 \text{ mH}$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left( \frac{BVDSS}{BVDSS - V_{DD}} \right)$$

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